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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	6000
Number of Logic Elements/Cells	24000
Total RAM Bits	1032192
Number of I/O	118
Number of Gates	-
Voltage - Supply	1.045V ~ 1.155V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	285-LFBGA, CSPBGA
Supplier Device Package	285-CSFBGA (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lfe5u-25f-7mg285c

Figures

2. Architecture

2.1. Overview

Each ECP5/ECP5-5G device contains an array of logic blocks surrounded by Programmable I/O Cells (PIC). Interspersed between the rows of logic blocks are rows of sysMEM™ Embedded Block RAM (EBR) and rows of sysDSP™ Digital Signal Processing slices, as shown in Figure 2.1 on page 13. The LFE5-85 devices have three rows of DSP slices, the LFE5-45 devices have two rows, and both LFE5-25 and LFE5-12 devices have one. In addition, the LFE5UM/LFE5UM5G devices contain SERDES Duals on the bottom of the device.

The Programmable Functional Unit (PFU) contains the building blocks for logic, arithmetic, RAM and ROM functions. The PFU block is optimized for flexibility, allowing complex designs to be implemented quickly and efficiently. Logic Blocks are arranged in a two-dimensional array.

The ECP5/ECP5-5G devices contain one or more rows of sysMEM EBR blocks. sysMEM EBRs are large, dedicated 18 Kb fast memory blocks. Each sysMEM block can be configured in a variety of depths and widths as RAM or ROM. In addition, ECP5/ECP5-5G devices contain up to three rows of DSP slices. Each DSP slice has multipliers and adder/accumulators, which are the building blocks for complex signal processing capabilities.

The ECP5 devices feature up to four embedded 3.2 Gb/s SERDES channels, and the ECP5-5G devices feature up to four embedded 5 Gb/s SERDES channels. Each SERDES channel contains independent 8b/10b encoding / decoding, polarity adjust and elastic buffer logic. Each group of two SERDES channels, along with its Physical Coding Sublayer (PCS) block, creates a dual DCU (Dual Channel Unit). The functionality of the SERDES/PCS duals can be controlled by SRAM cell settings during device configuration or by registers that are addressable during device operation. The registers in every dual can be programmed via the SERDES Client Interface (SCI). These DCUs (up to two) are located at the bottom of the devices.

Each PIC block encompasses two PIOs (PIO pairs) with their respective sysI/O buffers. The sysI/O buffers of the ECP5/ECP5-5G devices are arranged in seven banks (eight banks for LFE5-85 devices in caBGA756 and caBGA554 packages), allowing the implementation of a wide variety of I/O standards. One of these banks (Bank 8) is shared with the programming interfaces. Half of the PIO pairs on the left and right edges of the device can be configured as LVDS transmit pairs, and all pairs on left and right can be configured as LVDS receive pairs. The PIC logic in the left and right banks also includes pre-engineered support to aid in the implementation of high speed source synchronous standards such as XGMII, 7:1 LVDS, along with memory interfaces including DDR3 and LPDDR3.

The ECP5/ECP5-5G registers in PFU and sysI/O can be configured to be SET or RESET. After power up and the device is configured, it enters into user mode with these registers SET/RESET according to the configuration setting, allowing the device entering to a known state for predictable system function.

Other blocks provided include PLLs, DLLs and configuration functions. The ECP5/ECP5-5G architecture provides up to four Delay-Locked Loops (DLLs) and up to four Phase-Locked Loops (PLLs). The PLL and DLL blocks are located at the corners of each device.

The configuration block that supports features such as configuration bit-stream decryption, transparent updates and dual-boot support is located at the bottom of each device, to the left of the SERDES blocks. Every device in the ECP5/ECP5-5G family supports a sysCONFIG™ ports located in that same corner, powered by Vccio8, allowing for serial or parallel device configuration.

In addition, every device in the family has a JTAG port. This family also provides an on-chip oscillator and soft error detect capability. The ECP5 devices use 1.1 V and ECP5UM5G devices use 1.2 V as their core voltage.

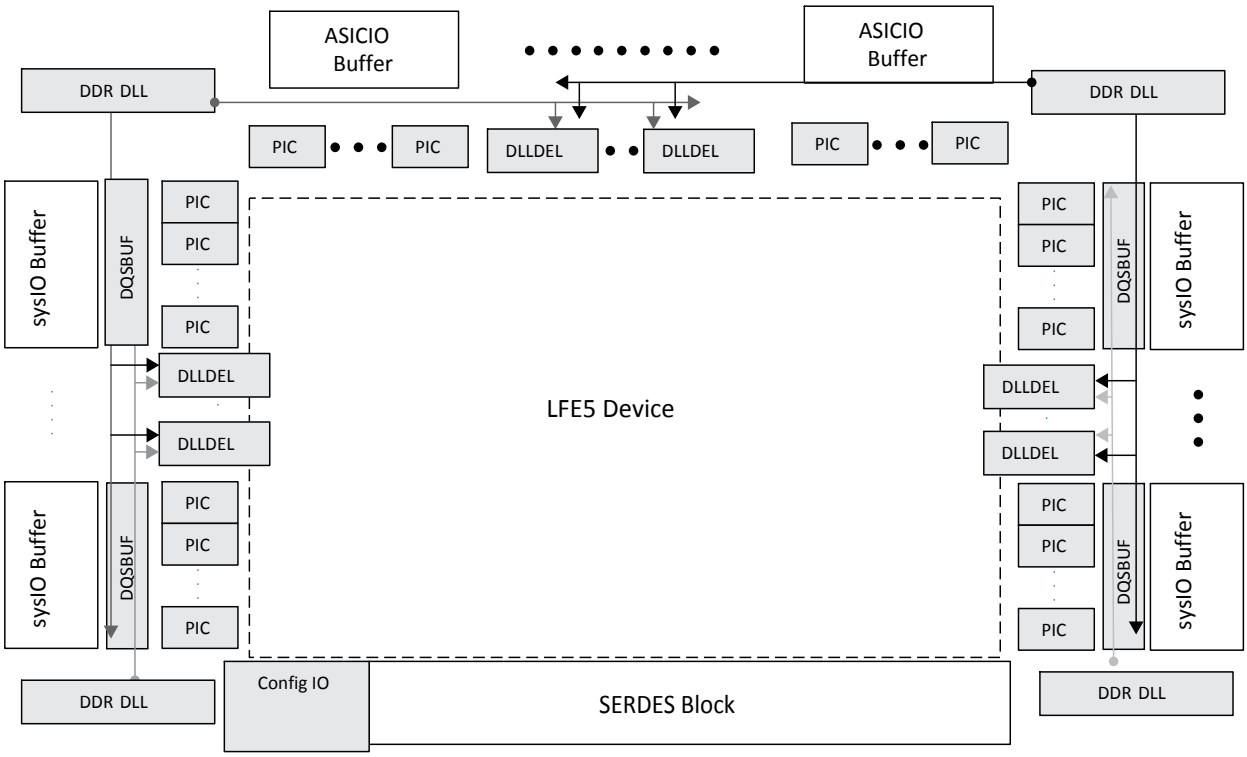


Figure 2.11. ECP5/ECP5-5G DLL Top Level View (For LFE-45 and LFE-85)

2.8. sysMEM Memory

ECP5/ECP5-5G devices contain a number of sysMEM Embedded Block RAM (EBR). The EBR consists of an 18 Kb RAM with memory core, dedicated input registers and output registers with separate clock and clock enable. Each EBR includes functionality to support true dual-port, pseudo dual-port, single-port RAM, ROM and FIFO buffers (via external PFUs).

2.8.1. sysMEM Memory Block

The sysMEM block can implement single port, dual port or pseudo dual port memories. Each block can be used in a variety of depths and widths as listed in Table 2.6 on page 25. FIFOs can be implemented in sysMEM EBR blocks by implementing support logic with PFUs. The EBR block facilitates parity checking by supporting an optional parity bit for each data byte. EBR blocks provide byte-enable support for configurations with 18-bit and 36-bit data widths. For more information, refer to ECP5 and ECP5-5G Memory Usage Guide (TN1264).

2.8.6. Memory Core Reset

The memory array in the EBR utilizes latches at the A and B output ports. These latches can be reset asynchronously or synchronously. RSTA and RSTB are local signals, which reset the output latches associated with Port A and Port B, respectively. The Global Reset (GSRN) signal can reset both ports. The output data latches and associated resets for both ports are as shown in Figure 2.12.

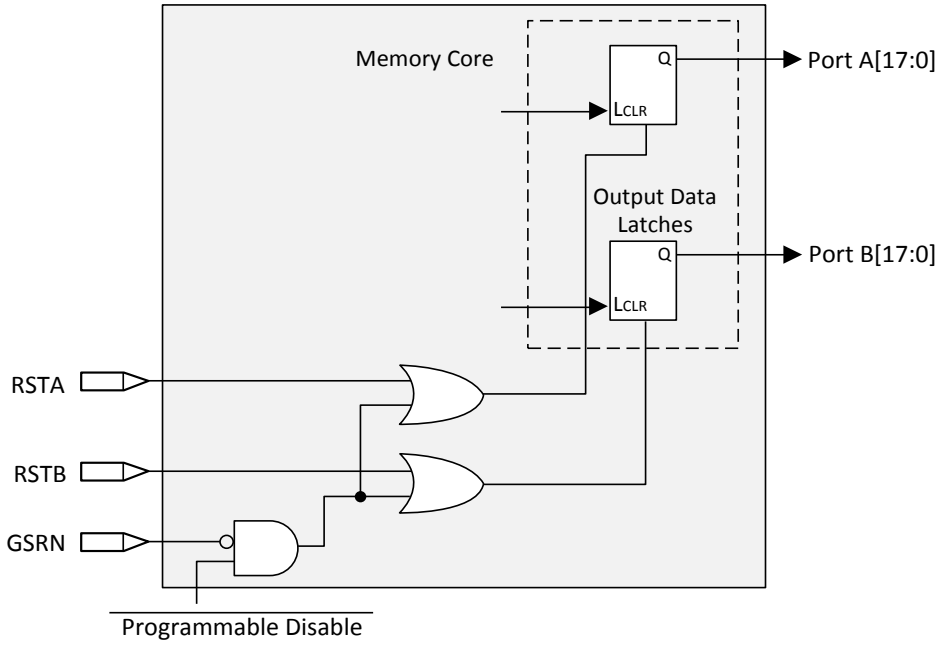


Figure 2.12. Memory Core Reset

For further information on the sysMEM EBR block, see the list of technical documentation in Supplemental Information section on page 102.

2.9. sysDSP™ Slice

The ECP5/ECP5-5G family provides an enhanced sysDSP architecture, making it ideally suited for low-cost, high-performance Digital Signal Processing (DSP) applications. Typical functions used in these applications are Finite Impulse Response (FIR) filters, Fast Fourier Transforms (FFT) functions, Correlators, Reed-Solomon/Turbo/Convolution encoders and decoders. These complex signal processing functions use similar building blocks such as multiply-adders and multiply-accumulators.

2.9.1. sysDSP Slice Approach Compared to General DSP

Conventional general-purpose DSP chips typically contain one to four (Multiply and Accumulate) MAC units with fixed data-width multipliers; this leads to limited parallelism and limited throughput. Their throughput is increased by higher clock speeds. In the ECP5/ECP5-5G device family, there are many DSP slices that can be used to support different data widths. This allows designers to use highly parallel implementations of DSP functions. Designers can optimize DSP performance vs. area by choosing appropriate levels of parallelism. Figure 2.13 compares the fully serial implementation to the mixed parallel and serial implementation.

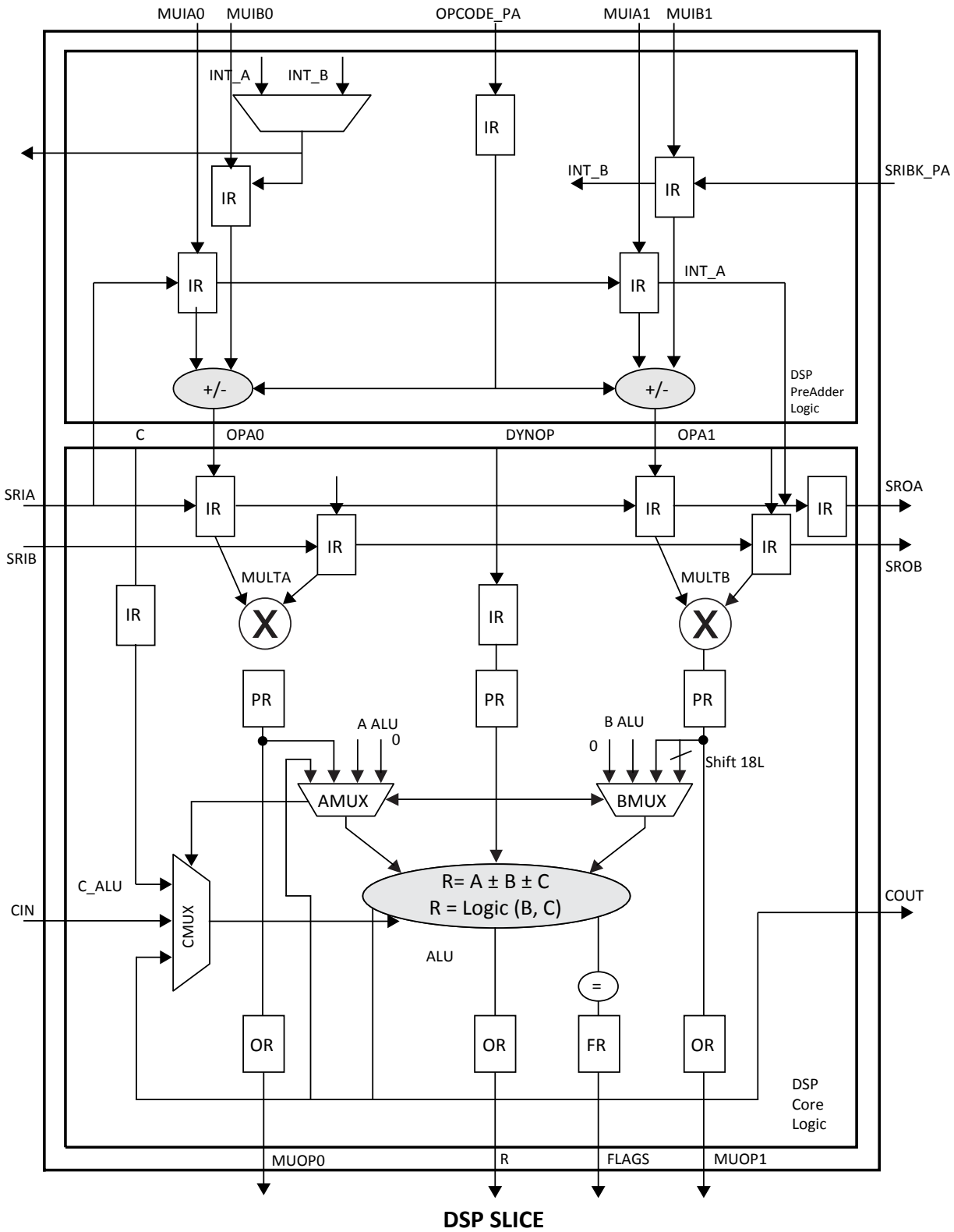


Figure 2.15. Detailed sysDSP Slice Diagram

2.14.4. On-Chip Programmable Termination

The ECP5/ECP5-5G devices support a variety of programmable on-chip terminations options, including:

- Dynamically switchable Single-Ended Termination with programmable resistor values of 50 Ω, 75 Ω, or 150 Ω.
- Common mode termination of 100 Ω for differential inputs.

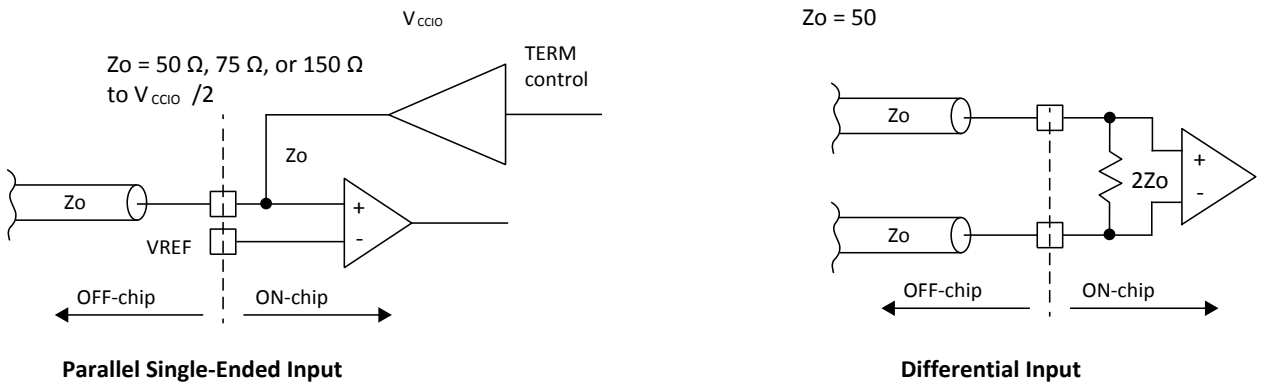


Figure 2.26. On-Chip Termination

See Table 2.12 for termination options for input modes.

Table 2.12. On-Chip Termination Options for Input Modes

IO_TYPE	Terminate to $V_{CCIO}/2$*	Differential Termination Resistor*
LVDS25	—	100
BLVDS25	—	100
MLVDS	—	100
LVPECL33	—	100
subLVDS	—	100
SLVS	—	100
HSUL12	50, 75, 150	—
HSUL12D	—	100
SSTL135_I / II	50, 75, 150	—
SSTL135D_I / II	—	100
SSTL15_I / II	50, 75, 150	—
SSTL15D_I / II	—	100
SSTL18_I / II	50, 75, 150	—
SSTL18D_I / II	—	100

***Notes**:

TERMINATE to $V_{CCIO}/2$ (Single-Ended) and DIFFRENTIAL TERMINATION RESISTOR when turned on can only have one setting per bank. Only left and right banks have this feature.

Use of TERMINATE to $V_{CCIO}/2$ and DIFFRENTIAL TERMINATION RESISTOR are mutually exclusive in an I/O bank. On-chip termination tolerance ±20%.

Refer to ECP5 and ECP5-5G sysIO Usage Guide (TN1262) for on-chip termination usage and value ranges.

2.14.5. Hot Socketing

ECP5/ECP5-5G devices have been carefully designed to ensure predictable behavior during power-up and power-down. During power-up and power-down sequences, the I/Os remain in tristate until the power supply voltage is high enough to ensure reliable operation. In addition, leakage into I/O pins is controlled within specified limits. See the Hot Socketing Specifications section on page 48.

3.7. Hot Socketing Requirements

Table 3.6. Hot Socketing Requirements

Description	Min	Typ	Max	Unit
Input current per SERDES I/O pin when device is powered down and inputs driven.	—	—	8	mA
Input current per HDIN pin when device power supply is off, inputs driven[1, 2]	—	—	15	mA
Current per HDIN pin when device power ramps up, input driven[3]	—	—	50	mA
Current per HDOUT pin when device power supply is off, outputs pulled up[4]	—	—	30	mA

Notes:

1. Device is powered down with all supplies grounded, both HDINP and HDINN inputs driven by a CML driver with maximum allowed output V_{CCHTX}, 8b/10b data, no external AC coupling.
2. Each P and N input must have less than the specified maximum input current during hot plug. For a device with 2 DCU, the total input current would be 15 mA * 4 channels * 2 input pins per channel = 120 mA.
3. Device power supplies are ramping up (V_{CCA} and V_{CCAUX}), both HDINP and HDINN inputs are driven by a CML driver with maximum allowed output V_{CCHTX}, 8b/10b data, internal AC coupling.
4. Device is powered down with all supplies grounded. Both HDOUTP and HDOUN outputs are pulled up to V_{CCHTX} by the far end receiver termination of 50 Ω single ended.

3.8. ESD Performance

Refer to the ECP5 and ECP5-5G Product Family Qualification Summary for complete qualification data, including ESD performance.

3.9. DC Electrical Characteristics

Over Recommended Operating Conditions

Table 3.7. DC Electrical Characteristics

Symbol	Parameter	Condition	Min	Typ	Max	Unit
I_{IL}, I_{IH}[1, 4]	Input or I/O Low Leakage	$0 \le V_{IN} \le V_{CCIO}$	—	—	10	µA
I_{IH}[1, 3]	Input or I/O High Leakage	$V_{CCIO} < V_{IN} \le V_{IH(MAX)}$	—	—	100	µA
I_{PU}	I/O Active Pull-up Current, sustaining logic HIGH state	$0.7\ V_{CCIO} \le V_{IN} \le V_{CCIO}$	–30	—	—	µA
	I/O Active Pull-up Current, pulling down from logic HIGH state	$0 \le V_{IN} \le 0.7\ V_{CCIO}$	—	—	–150	µA
I_{PD}	I/O Active Pull-down Current, sustaining logic LOW state	$0 \le V_{IN} \le V_{IL}$ (MAX)	30	—	—	µA
	I/O Active Pull-down Current, pulling up from logic LOW state	$0 \le V_{IN} \le V_{CCIO}$	—	—	150	µA
C1	I/O Capacitance[2]	V_{CCIO} = 3.3 V, 2.5 V, 1.8 V, 1.5 V, 1.2 V, V_{CC} = 1.2 V, V_{IO} = 0 to $V_{IH(MAX)}$	—	5	8	pf
C2	Dedicated Input Capacitance[2]	V_{CCIO} = 3.3 V, 2.5 V, 1.8 V, 1.5 V, 1.2 V, V_{CC} = 1.2 V, V_{IO} = 0 to $V_{IH(MAX)}$	—	5	7	pf
V_{HYST}	Hysteresis for Single-Ended Inputs	V_{CCIO} = 3.3 V	—	300	—	mV
		V_{CCIO} = 2.5 V	—	250	—	mV

Notes:

1. Input or I/O leakage current is measured with the pin configured as an input or as an I/O with the output driver tristated. It is not measured with the output driver active. Bus maintenance circuits are disabled.
2. T_A 25 °C, f = 1.0 MHz.
3. Applicable to general purpose I/Os in top and bottom banks.
4. When used as V_{REF}, maximum leakage= 25 µA.

3.12. sysI/O Recommended Operating Conditions

Table 3.11. sysI/O Recommended Operating Conditions

Standard	V_{CCIO}			V_{REF} (V)		
	Min	Typ	Max	Min	Typ	Max
LVCMOS33[1]	3.135	3.3	3.465	—	—	—
LVCMOS33D[3] Output	3.135	3.3	3.465	—	—	—
LVCMOS25[1]	2.375	2.5	2.625	—	—	—
LVCMOS18	1.71	1.8	1.89	—	—	—
LVCMOS15	1.425	1.5	1.575	—	—	—
LVCMOS12[1]	1.14	1.2	1.26	—	—	—
LVTTL33[1]	3.135	3.3	3.465	—	—	—
SSTL15_I, _II[2]	1.43	1.5	1.57	0.68	0.75	0.9
SSTL18_I, _II[2]	1.71	1.8	1.89	0.833	0.9	0.969
SSTL135_I, _II[2]	1.28	1.35	1.42	0.6	0.675	0.75
HSUL12[2]	1.14	1.2	1.26	0.588	0.6	0.612
MIPI D-PHY LP Input[3, 5]	1.425	1.5	1.575	—	—	—
LVDS25[1, 3] Output	2.375	2.5	2.625	—	—	—
subLVS[3] (Input only)	—	—	—	—	—	—
SLVS[3] (Input only)	—	—	—	—	—	—
LVDS25E[3] Output	2.375	2.5	2.625	—	—	—
MLVDS[3] Output	2.375	2.5	2.625	—	—	—
LVPECL33[1, 3] Output	3.135	3.3	3.465	—	—	—
BLVDS25[1, 3] Output	2.375	2.5	2.625	—	—	—
HSULD12D[2, 3]	1.14	1.2	1.26	—	—	—
SSTL135D_I, II[2, 3]	1.28	1.35	1.42	—	—	—
SSTL15D_I, II[2, 3]	1.43	1.5	1.57	—	—	—
SSTL18D_I[1, 2, 3], II[1, 2, 3]	1.71	1.8	1.89	—	—	—

Notes:

1. For input voltage compatibility, refer to ECP5 and ECP5-5G sysIO Usage Guide (TN1262).
2. V_{REF} is required when using Differential SSTL and HSUL to interface to DDR/LPDDR memories.
3. These differential inputs use LVDS input comparator, which uses V_{CCAUX} power
4. All differential inputs and LVDS25 output are supported in the Left and Right banks only. Refer to ECP5 and ECP5-5G sysIO Usage Guide (TN1262) for details.
5. MIPI D-PHY LP input can be implemented by powering VCCIO to 1.5V, and select MIPI LP primitive to meet MIPI Alliance spec on V_{IH} and V_{IL}. It can also be implemented as LVCMOS12 with VCCIO at 1.2V, which would meet V_{IH}/V_{IL} spec on LVCOM12.

3.25. PCI Express Electrical and Timing Characteristics

3.25.1. PCIe (2.5 Gb/s) AC and DC Characteristics

Over recommended operating conditions.

Table 3.30. PCIe (2.5 Gb/s)

Symbol	Description	Test Conditions	Min	Typ	Max	Unit
Transmit[1]						
UI	Unit interval	—	399.88	400	400.12	ps
$V_{TX-DIFF\_P-P}$	Differential peak-to-peak output	—	0.8	1.0	1.2	V
$V_{TX-DE-RATIO}$	De-emphasis differential output voltage ratio	—	–3	–3.5	–4	dB
$V_{TX-CM-AC\_P}$	RMS AC peak common-mode output voltage	—	—	—	20	mV
$V_{TX-RCV-DETECT}$	Amount of voltage change allowed during receiver detection	—	—	—	600	mV
$V_{TX-CM-DC}$	Tx DC common mode voltage	—	0	—	V_{CCHTX}	V
$I_{TX-SHORT}$	Output short circuit current	V_{TX-D+}=0.0 V V_{TX-D-}=0.0 V	—	—	90	mA
$Z_{TX-DIFF-DC}$	Differential output impedance	—	80	100	120	Ω
$RL_{TX-DIFF}$	Differential return loss	—	10	—	—	dB
RL_{TX-CM}	Common mode return loss	—	6.0	—	—	dB
$T_{TX-RISE}$	Tx output rise time	20% to 80%	0.125	—	—	UI
$T_{TX-FALL}$	Tx output fall time	20% to 80%	0.125	—	—	UI
$L_{TX-SKEW}$	Lane-to-lane static output skew for all lanes in port/link	—	—	—	1.3	ns
T_{TX-EYE}	Transmitter eye width	—	0.75	—	—	UI
$T_{TX-EYE-MEDIAN-TO-MAX-JITTER}$	Maximum time between jitter median and maximum deviation from median	—	—	—	0.125	UI
Receive[1, 2]						
UI	Unit Interval	—	399.88	400	400.12	ps
$V_{RX-DIFF\_P-P}$	Differential peak-to-peak input voltage	—	0.34[3]	—	1.2	V
$V_{RX-IDLE-DET-DIFF\_P-P}$	Idle detect threshold voltage	—	65	—	340[3]	mV
$V_{RX-CM-AC\_P}$	RMS AC peak common-mode input voltage	—	—	—	150	mV
$Z_{RX-DIFF-DC}$	DC differential input impedance	—	80	100	120	Ω
Z_{RX-DC}	DC input impedance	—	40	50	60	Ω
$Z_{RX-HIGH-IMP-DC}$	Power-down DC input impedance	—	200K	—	—	Ω
$RL_{RX-DIFF}$	Differential return loss	—	10	—	—	dB
RL_{RX-CM}	Common mode return loss	—	6.0	—	—	dB

Notes:

1. Values are measured at 2.5 Gb/s.
2. Measured with external AC-coupling on the receiver.
3. Not in compliance with PCI Express 1.1 standard.

3.25.2. PCIe (5 Gb/s) – Preliminary AC and DC Characteristics

Over recommended operating conditions.

Table 3.31. PCIe (5 Gb/s)

Symbol	Description	Test Conditions	Min	Typ	Max	Unit
Transmit[1]						
UI	Unit Interval	—	199.94	200	200.06	ps
$B_{WTX-PKG-PLL2}$	Tx PLL bandwidth corresponding to PKGTX-PLL2	—	5	—	16	MHz
$P_{KGTX-PLL2}$	Tx PLL Peaking	—	—	—	1	dB
$V_{TX-DIFF-PP}$	Differential p-p Tx voltage swing	—	0.8	—	1.2	V, p-p
$V_{TX-DIFF-PP-LOW}$	Low power differential p-p Tx voltage swing	—	0.4	—	1.2	V, p-p
$V_{TX-DE-RATIO-3.5dB}$	Tx de-emphasis level ratio at 3.5dB	—	3	—	4	dB
$V_{TX-DE-RATIO-6dB}$	Tx de-emphasis level ratio at 6dB	—	5.5	—	6.5	dB
$T_{MIN-PULSE}$	Instantaneous lone pulse width	—		—	—	UI
$T_{TX-RISE-FALL}$	Transmitter rise and fall time	—		—	—	UI
T_{TX-EYE}	Transmitter Eye, including all jitter sources	—	0.75	—	—	UI
T_{TX-DJ}	Tx deterministic jitter > 1.5 MHz	—	—	—	0.15	UI
T_{TX-RJ}	Tx RMS jitter < 1.5 MHz	—	—	—	3	ps, RMS
$T_{RF-MISMATCH}$	Tx rise/fall time mismatch	—	—	—		UI
$R_{LTX-DIFF}$	Tx Differential Return Loss, including package and silicon	50 MHz < freq < 1.25 GHz	10	—	—	dB
		1.25 GHz < freq < 2.5 GHz	8	—	—	dB
R_{LTX-CM}	Tx Common Mode Return Loss, including package and silicon	50 MHz < freq < 2.5 GHz	6	—	—	dB
$Z_{TX-DIFF-DC}$	DC differential Impedance	—	—	—	120	Ω
$V_{TX-CM-AC-PP}$	Tx AC peak common mode voltage, peak-peak	—	—	—		mV, p-p
$I_{TX-SHORT}$	Transmitter short-circuit current	—	—	—	90	mA
$V_{TX-DC-CM}$	Transmitter DC common-mode voltage	—	0	—	1.2	V
$V_{TX-IDLE-DIFF-DC}$	Electrical Idle Output DC voltage	—	0	—	5	mV
$V_{TX-IDLE-DIFF-AC-p}$	Electrical Idle Differential Output peak voltage	—	—	—		mV
$V_{TX-RCV-DETECT}$	Voltage change allowed during Receiver Detect	—	—	—	600	mV
$T_{TX-IDLE-MIN}$	Min. time in Electrical Idle	—	20	—	—	ns
$T_{TX-IDLE-SET-TO-IDLE}$	Max. time from EI Order Set to valid Electrical Idle	—	—	—	8	ns
$T_{TX-IDLE-TO-DIFF-DATA}$	Max. time from Electrical Idle to valid differential output	—	—	—	8	ns
$L_{TX-SKEW}$	Lane-to-lane output skew	—	—	—		ps

3.26. CPRI LV2 E.48 Electrical and Timing Characteristics – Preliminary

Table 3.32. CPRI LV2 E.48 Electrical and Timing Characteristics

Symbol	Description	Test Conditions	Min	Typ	Max	Unit
Transmit						
UI	Unit Interval	—	203.43	203.45	203.47	ps
T_{DCD}	Duty Cycle Distortion	—	—	—	0.05	UI
J_{UBHPJ}	Uncorrelated Bounded High Probability Jitter	—	—	—	0.15	UI
J_{TOTAL}	Total Jitter	—	—	—	0.3	UI
$Z_{RX-DIFF-DC}$	DC differential Impedance	—	80	—	120	Ω
T_{SKEW}	Skew between differential signals	—	—	—	9	ps
$R_{LTX-DIFF}$	Tx Differential Return Loss (S22), including package and silicon	100 MHz < freq < 3.6864 GHz	—	—	–8	dB
		3.6864 GHz < freq < 4.9152 GHz	—	—	–8 + 16.6 *log (freq/3.6864)	dB
R_{LTX-CM}	Tx Common Mode Return Loss, including package and silicon	100 MHz < freq < 3.6864 GHz	6	—	—	dB
$I_{TX-SHORT}$	Transmitter short-circuit current	—	—	—	100	mA
$T_{RISE\_FALL-DIFF}$	Differential Rise and Fall Time	—		—	—	ps
$L_{TX-SKEW}$	Lane-to-lane output skew	—	—	—		ps
Receive						
UI	Unit Interval	—	203.43	203.45	203.47	ps
$V_{RX-DIFF-PP}$	Differential Rx peak-peak voltage	—	—	—	1.2	V, p-p
$V_{RX-EYE\_Y1\_Y2}$	Receiver eye opening mask, Y1 and Y2	—	62.5	—	375	mV, diff
V_{RX-EYE_X1}	Receiver eye opening mask, X1	—	—	—	0.3	UI
T_{RX-TJ}	Receiver total jitter tolerance (not including sinusoidal)	—	—	—	0.6	UI
$R_{LRX-DIFF}$	Receiver differential Return Loss, package plus silicon	100 MHz < freq < 3.6864 GHz	—	—	–8	dB
		3.6864 GHz < freq < 4.9152 GHz	—	—	–8 + 16.6 *log (freq/3.6864)	dB
R_{LRX-CM}	Receiver common mode Return Loss, package plus silicon	—	6	—	—	dB
$Z_{RX-DIFF-DC}$	Receiver DC differential impedance	—	80	100	120	Ω

Note: Data is measured with PRBS7 data pattern, not with PRBS-31 pattern.

3.27. XAUI/CPRI LV E.30 Electrical and Timing Characteristics

3.27.1. AC and DC Characteristics

Over recommended operating conditions.

Table 3.33. Transmit

Symbol	Description	Test Conditions	Min	Typ	Max	Unit
T_{RF}	Differential rise/fall time	20% to 80%	—	80	—	ps
$Z_{TX\_DIFF\_DC}$	Differential impedance	—	80	100	120	Ω
J_{TX_DDJ}[2, 3]	Output data deterministic jitter	—	—	—	0.17	UI
J_{TX_TJ}[1, 2, 3]	Total output data jitter	—	—	—	0.35	UI

Notes:
1. Total jitter includes both deterministic jitter and random jitter.
2. Jitter values are measured with each CML output AC coupled into a 50 Ω impedance (100 Ω differential impedance).
3. Jitter and skew are specified between differential crossings of the 50% threshold of the reference signal.

Over recommended operating conditions.

Table 3.34. Receive and Jitter Tolerance

Symbol	Description	Test Conditions	Min	Typ	Max	Unit
RL_{RX_DIFF}	Differential return loss	From 100 MHz to 3.125 GHz	10	—	—	dB
RL_{RX_CM}	Common mode return loss	From 100 MHz to 3.125 GHz	6	—	—	dB
Z_{RX_DIFF}	Differential termination resistance	—	80	100	120	Ω
J_{RX_DJ}[1, 2, 3]	Deterministic jitter tolerance (peak-to-peak)	—	—	—	0.37	UI
J_{RX_RJ}[1, 2, 3]	Random jitter tolerance (peak-to-peak)	—	—	—	0.18	UI
J_{RX_SJ}[1, 2, 3]	Sinusoidal jitter tolerance (peak-to-peak)	—	—	—	0.10	UI
J_{RX_TJ}[1, 2, 3]	Total jitter tolerance (peak-to-peak)	—	—	—	0.65	UI
T_{RX_EYE}	Receiver eye opening	—	0.35	—	—	UI

Notes:
1. Total jitter includes deterministic jitter, random jitter and sinusoidal jitter.
2. Jitter values are measured with each high-speed input AC coupled into a 50 Ω impedance.
3. Jitter and skew are specified between differential crossings of the 50% threshold of the reference signal.

3.28. CPRI LV E.24/SGMII(2.5Gbps) Electrical and Timing Characteristics

3.28.1. AC and DC Characteristics

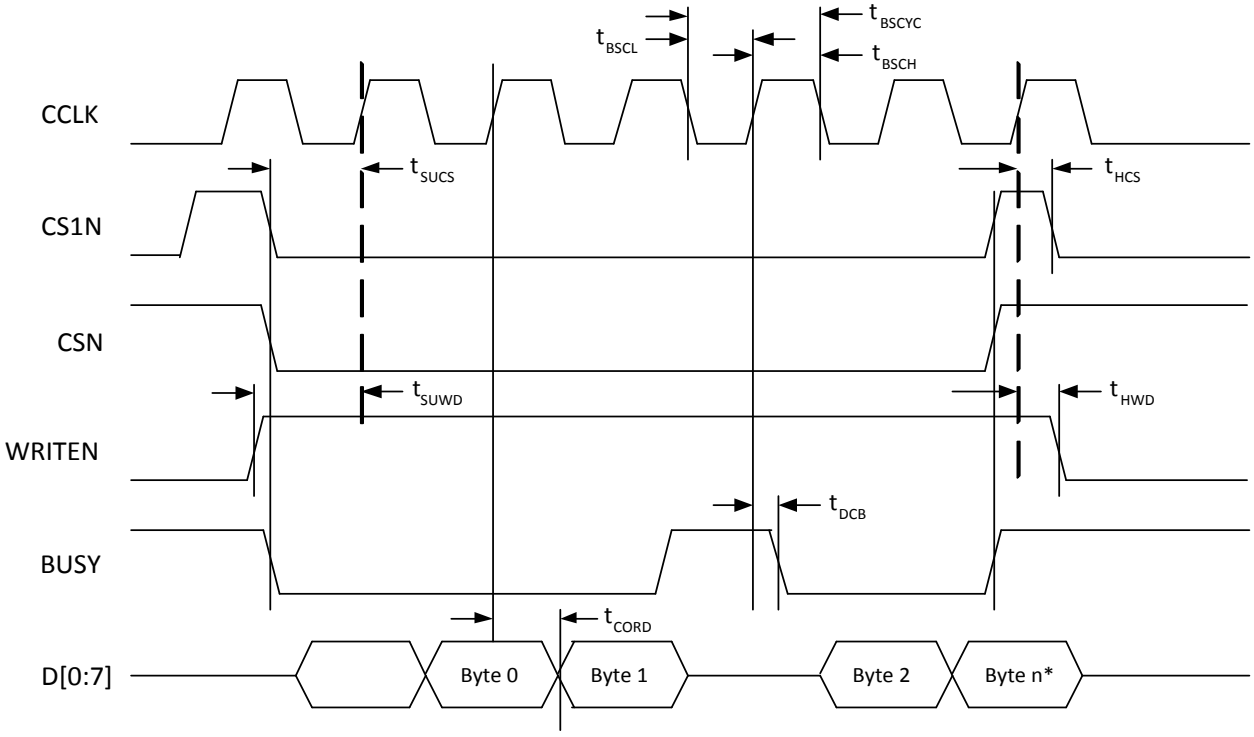
Table 3.35. Transmit

Symbol	Description	Test Conditions	Min	Typ	Max	Unit
T_{RF}[1]	Differential rise/fall time	20% to 80%	—	80	—	ps
$Z_{TX\_DIFF\_DC}$	Differential impedance	—	80	100	120	Ω
J_{TX_DDJ}[3, 4]	Output data deterministic jitter	—	—	—	0.17	UI
J_{TX_TJ}[2, 3, 4]	Total output data jitter	—	—	—	0.35	UI

Notes:
1. Rise and Fall times measured with board trace, connector and approximately 2.5 pf load.
2. Total jitter includes both deterministic jitter and random jitter. The random jitter is the total jitter minus the actual deterministic jitter.
3. Jitter values are measured with each CML output AC coupled into a 50 Ω impedance (100 Ω differential impedance).
4. Jitter and skew are specified between differential crossings of the 50% threshold of the reference signal.

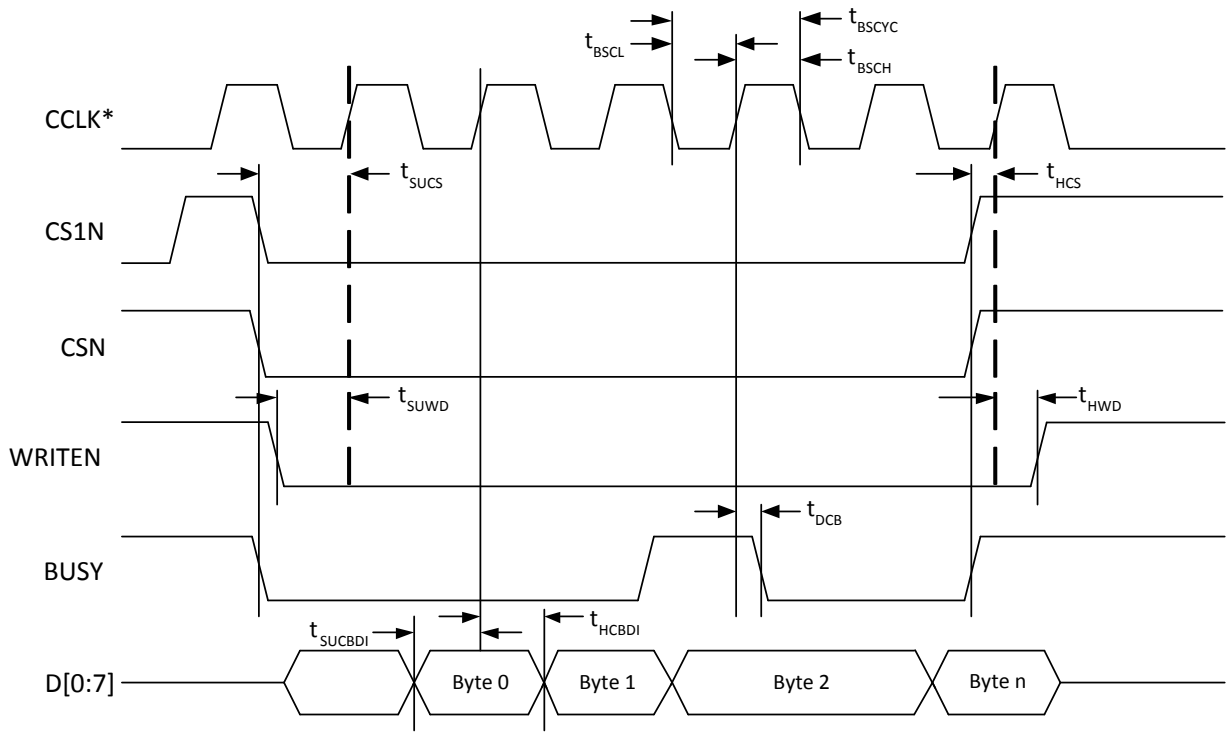
Table 3.42. ECP5/ECP5-5G sysCONFIG Port Timing Specifications *(Continued)*

Symbol	Parameter		Min	Max	Unit
Slave Parallel					
f_{CCLK}	CCLK input clock frequency	—	—	50	MHz
t_{BSCH}	CCLK input clock pulsewidth HIGH	—	6	—	ns
t_{BSCL}	CCLK input clock pulsewidth LOW	—	6	—	ns
t_{CORD}	CCLK to DOUT for Read Data	—	—	12	ns
t_{SUCBDI}	Data Setup Time to CCLK	—	1.5	—	ns
t_{HCBDI}	Data Hold Time to CCLK	—	1.5	—	ns
t_{SUCS}	CSN, CSN1 Setup Time to CCLK	—	2.5	—	ns
t_{HCS}	CSN, CSN1 Hold Time to CCLK	—	1.5	—	ns
t_{SUWD}	WRITEN Setup Time to CCLK	—	45	—	ns
t_{HCWD}	WRITEN Hold Time to CCLK	—	2	—	ns
t_{DCB}	CCLK to BUSY Delay Time	—	—	12	ns



*n = last byte of read cycle.

Figure 3.15. sysCONFIG Parallel Port Read Cycle



*In Master Parallel Mode the FPGA provides CCLK (MCLK). In Slave Parallel Mode the external device provides CCLK.

Figure 3.16. sysCONFIG Parallel Port Write Cycle

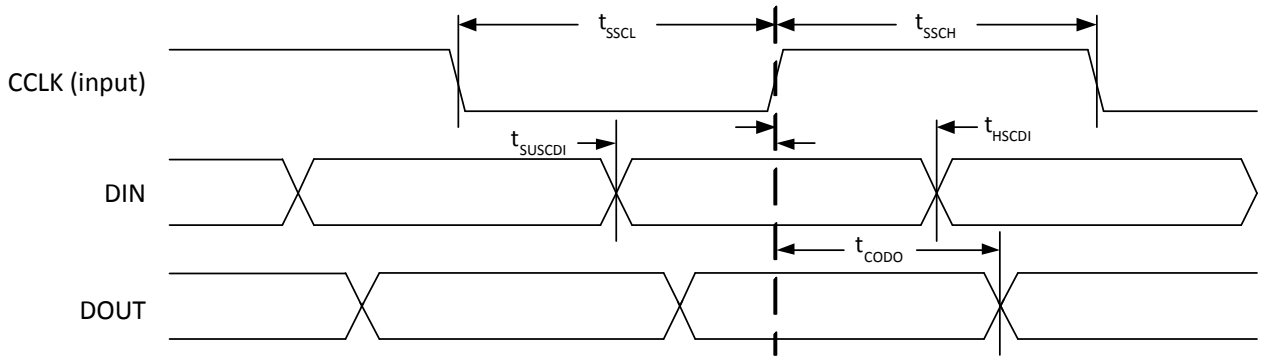


Figure 3.17. sysCONFIG Slave Serial Port Timing

Pin Information Summary		LFE5UM/ LFE5UM5G-25		LFE5UM/LFE5UM5G-45			LFE5UM/LFE5UM5G-85			
Pin Type		285 csfBG	381 caBGA	285 csfBGA	381 caBG	554 caBGA	285 csfBGA	381 caBG	554 caBGA	756 caBGA
TAP		4	4	4	4	4	4	4	4	4
Miscellaneous Dedicated Pins		7	7	7	7	7	7	7	7	7
GND		83	59	83	59	113	83	59	113	166
NC		1	8	1	2	33	1	0	17	29
Reserved		0	2	0	2	4	0	2	4	4
SERDES		14	28	14	28	28	14	28	28	28
VCCA (SERDES)	VCCA0	2	2	2	2	6	2	2	6	8
	VCCA1	0	2	0	2	6	0	2	6	9
VCCAUX (SERDES)	VCCAUXA0	2	2	2	2	2	2	2	2	2
	VCCAUXA1	0	2	0	2	2	0	2	2	2
GNDA (SERDES)		26	26	26	26	49	26	26	49	60
Total Balls		285	381	285	381	554	285	381	554	756
High Speed Differential Input / Output Pairs	Bank 0	0	0	0	0	0	0	0	0	0
	Bank 1	0	0	0	0	0	0	0	0	0
	Bank 2	10/8	16/8	10/8	16/8	16/8	10/8	17/9	16/8	24/12
	Bank 3	14/7	16/8	14/7	16/8	24/12	14/7	16/8	24/12	32/16
	Bank 4	0	0	0	0	0	0	0	0	0
	Bank 6	13/6	16/8	13/6	16/8	24/12	13/6	16/8	24/12	32/16
	Bank 7	8/6	16/8	8/6	16/8	16/8	8/6	16/8	16/8	24/12
	Bank 8	0	0	0	0	0	0	0	0	0
Total High Speed Differential I/O Pairs		45/2	64/32	45/27	64/3	80/40	45/27	65/3	80/40	112/5
DQS Groups (> 11 pins in group)	Bank 0	0	0	0	0	0	0	0	0	0
	Bank 1	0	0	0	0	0	0	0	0	0
	Bank 2	1	2	1	2	2	1	2	2	3
	Bank 3	2	2	2	2	3	2	2	3	4
	Bank 4	0	0	0	0	0	0	0	0	0
	Bank 6	2	2	2	2	3	2	2	3	4
	Bank 7	1	2	1	2	2	1	2	2	3
	Bank 8	0	0	0	0	0	0	0	0	0
Total DQS Groups		6	8	6	8	10	6	8	10	14

4.3.2. LFE5U

Pin Information Summary		LFE5U-12			LFE5U-25			LFE5U-45				LFE5U-85			
Pin Type		256 caBGA	285 csfBGA	381 caBGA	256 caBGA	285 csfBGA	381 caBGA	256 caBGA	285 csfBGA	381 caBGA	554 caBGA	285 csfBG	381 caBGA	554 caBGA	756 caBG
General Purpose Inputs/Outputs per Bank	Bank 0	24	6	24	24	6	24	24	6	27	32	6	27	32	56
	Bank 1	32	6	32	32	6	32	32	6	33	40	6	33	40	48
	Bank 2	32	21	32	32	21	32	32	21	32	32	21	34	32	48
	Bank 3	32	28	32	32	28	32	32	28	33	48	28	33	48	64
	Bank 4	0	0	0	0	0	0	0	0	0	0	0	0	14	24
	Bank 6	32	26	32	32	26	32	32	26	33	48	26	33	48	64
	Bank 7	32	18	32	32	18	32	32	18	32	32	18	32	32	48
	Bank 8	13	13	13	13	13	13	13	13	13	13	13	13	13	13
Total Single-Ended User		197	118	197	197	118	197	197	118	203	245	118	205	259	365
VCC		6	13	20	6	13	20	6	13	20	24	13	20	24	36
VCCAUX (Core)		2	3	4	2	3	4	2	3	4	9	3	4	9	8
VCCIO	Bank 0	2	1	2	2	1	2	2	1	2	3	1	2	3	4
	Bank 1	2	1	2	2	1	2	2	1	2	3	1	2	3	4
	Bank 2	2	2	3	2	2	3	2	2	3	4	2	3	4	4
	Bank 3	2	2	3	2	2	3	2	2	3	3	2	3	3	4
	Bank 4	0	0	0	0	0	0	0	0	0	0	0	0	2	2
	Bank 6	2	2	3	2	2	3	2	2	3	4	2	3	4	4
	Bank 7	2	2	3	2	2	3	2	2	3	3	2	3	3	4
	Bank 8	1	2	2	1	2	2	1	2	2	2	2	2	2	2
TAP		4	4	4	4	4	4	4	4	4	4	4	4	4	4
Miscellaneous Dedicated		7	7	7	7	7	7	7	7	7	7	7	7	7	7
GND		27	123	99	27	123	99	27	123	99	198	123	99	198	267
NC		0	1	26	0	1	26	0	1	26	33	1	26	33	29
Reserved		0	4	6	0	4	6	0	4	6	12	4	6	12	12
Total Balls		256	285	381	256	285	381	256	285	381	554	285	381	554	756
High Speed Differential Input / Output Pairs	Bank	0	0	0	0	0	0	0	0	0	0	0	0	0	0
	Bank	0	0	0	0	0	0	0	0	0	0	0	0	0	0
	Bank	16/8	10/8	16/8	16/8	10/8	16/8	16/8	10/8	16/8	16/8	10/8	17/9	16/8	
	Bank	16/8	14/7	16/8	16/8	14/7	16/8	16/8	14/7	16/8	24/12	14/7	16/8	24/1	
	Bank	0	0	0	0	0	0	0	0	0	0	0	0	0	0
	Bank	16/8	13/6	16/8	16/8	13/6	16/8	16/8	13/6	16/8	24/12	13/6	16/8	24/1	
	Bank	16/8	8/6	16/8	16/8	8/6	16/8	16/8	8/6	16/8	16/8	8/6	16/8	16/8	
	Bank	0	0	0	0	0	0	0	0	0	0	0	0	0	0
Total High Speed		64/32	45/27	64/32	64/32	45/27	64/32	64/32	45/27	64/32	80/40	45/27	65/33	80/40	112/
DQS Groups (> 11 pins in group)	Bank	0	0	0	0	0	0	0	0	0	0	0	0	0	0
	Bank	0	0	0	0	0	0	0	0	0	0	0	0	0	0
	Bank	2	1	2	2	1	2	2	1	2	2	1	2	2	
	Bank	2	2	2	2	2	2	2	2	2	3	2	2	3	
	Bank	0	0	0	0	0	0	0	0	0	0	0	0	0	0
	Bank	2	2	2	2	2	2	2	2	2	3	2	2	3	
	Bank	2	1	2	2	1	2	2	1	2	2	1	2	2	
	Bank	0	0	0	0	0	0	0	0	0	0	0	0	0	0
Total DQS Groups		8	6	8	8	6	8	8	6	8	10	6	8	10	14

(Continued)

Date	Version	Section	Change Summary
April 2017	1.7	All	Changed document number from DS1044 to FPGA-DS-02012.
		General Description	Updated Features section. Changed “1.1 V core power supply” to “1.1 V core power supply for ECP5, 1.2 V core power supply for ECP5UM5G”.
		Architecture	Updated Overview section. Change “The ECP5/ECP5-5G devices use 1.1 V as their core voltage” to “The ECP5 devices use 1.1V, ECP5UM5G devices use 1.2V as their core voltage”
		DC and Switching Characteristics	Updated Table 3.2. Recommended Operating Conditions Added ECP5-5G on VCC to be 1.2V +/- 5% Added ECP5-5G on VCCA to be 1.2V +/- 3% Updated Table 3.8. ECP5/ECP5-5G Supply Current (Standby) Changed “Core Power Supply Current” for ICC on LFE5UM5G devices Changed “SERDES Power Supply Current (Per Dual)” for ICCA on LFE5UM5G devices Updated Table 3.20. Register-to-Register Performance. Remove “(DDR/SDR)” from DSP Function Changed DSP functions to 225 MHz
		Pinout Information	Update Section 4.1 Signal Description. Revised Vcc Description to “Power supply pins for core logic. Dedicated pins. VCC = 1.1 V (ECP5), 1.2 V (ECP5UM5G)”
February 2016	1.6	All	Changed document status from Preliminary to Final.
		General Description	Updated Features section. Changed “24K to 84K LUTs” to “12K to 84K LUTs”. Added LFE5U-12 column to Table 1.1. ECP5 and ECP5-5G Family Selection Guide.
		DC and Switching Characteristics	Updated Power up Sequence section. Identified typical ICC current for specific devices in Table 3.8. ECP5/ECP5-5G Supply Current (Standby). Updated values in Table 3.9. ECP5. Updated values in Table 3.10. ECP5-5G. Added values to –8 Timing column of Table 3.19. Pin-to-Pin Performance. Added values to –8 Timing column of Table 3.20. Register-to-Register Performance. Changed LFE5-45 to All Devices in Table 3.22. ECP5/ECP5-5G External Switching Characteristics. Added table notes to Table 3.31. PCIe (5 Gb/s). Added table note to Table 3.32. CPRI LV2 E.48 Electrical and Timing Characteristics.
		Pinout Information	Added LFE5U-12 column to the table in LFE5U section.
		Ordering Information	Updated LFE5U in ECP5/ECP5-5G Part Number Description section: added 12 F = 12K LUTs to Logic Capacity. Added LFE5U-12F information to Ordering Part Numbers section.

(Continued)

Date	Version	Section	Change Summary
November 2015	1.5	All	Added ECP5-5G device family.
			Changed document title to ECP5 and ECP5-5G Family Data Sheet.
	1.4	General Description	Updated Features section. Added support for eDP in RDR and HDR.
		Architecture	Updated Overview section. Revised Figure 2.1. Simplified Block Diagram, LFE5UM/LFE5UM5G-85 Device (Top Level). Modified Flexible sysIO description and Note.
			Updated SERDES and Physical Coding Sublayer section. • Changed E.24.V in CPRI protocol to E.24.LV. • Removed "1.1 V" from paragraph on unused Dual.
		DC and Switching Characteristics	Updated Hot Socketing Requirements section. Revised V_{CCHTX} in table notes 1 and 3. Indicated V_{CCHTX} in table note 4.
			Updated SERDES High-Speed Data Transmitter section. Revised V_{CCHTX} in table note 1.
		Ordering Information	Updated ECP5/ECP5-5G Part Number Description section. Changed "LFE5 FPGA" under Device Family to "ECP5 FPGA".
August 2015	1.3	General Description	Updated Features section. • Removed SMPTE3G under Embedded SERDES. • Added Single Event Upset (SEU) Mitigation Support. Removed SMPTE protocol in fifth paragraph.
		Architecture	General update.
		DC and Switching Characteristics	General update.
		Pinout Information	Updated Signal Descriptions section. Revised the descriptions of the following signals: • P[L/R] [Group Number]_[A/B/C/D] • P[T/B][Group Number]_[A/B] • D4/IO4 (Previously named D4/MOSI2/IO4) • D5/IO5 (Previously named D5/MISO/IO5) • VCCHRX_D[dual_num]CH[chan_num] • VCCHTX_D[dual_num]CH[chan_num]
		Supplemental Information	Added TN1184 reference.

7th Floor, 111 SW 5th Avenue
Portland, OR 97204, USA
T 503.268.8000
www.latticesemi.com